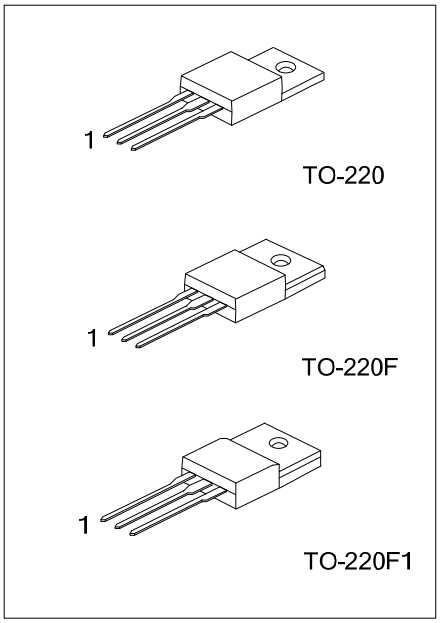
5A, 800V N-CHANNEL POWER MOSFET



■ DESCRIPTION

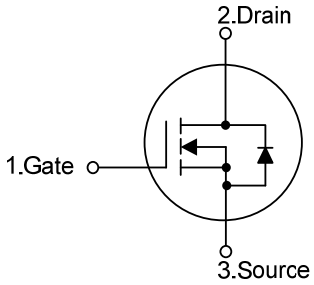
The UTC **5N80** is a N-channel enhancement mode power MOSFET. It use UTC advanced technology to provide avalanche rugged technology and low gate charge.

It can be applied in high current, high speed switching, switch mode power supplies (SMPS), consumer and industrial lighting, DC-AC inverters for welding equipment and uninterruptible power supply(UPS).

■ FEATURES

* $R_{DS(ON)}$: 2.0Ω (TYP.)
* Avalanche rugged technology
* Low input capacitance
* Low gate charge
* Application oriented characterization

■ SYMBOL



■ ORDERING INFORMATION

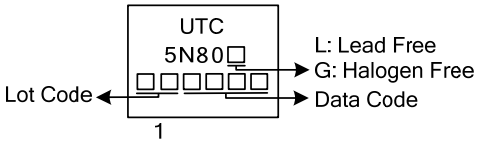
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
5N80L-TA3-T	5N80G-TA3-T	TO-220	G	D	S	Tube
5N80L-TF1-T	5N80G-TF1-T	TO-220F1	G	D	S	Tube
5N80L-TF3-T	5N80G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

5N80L-TA3-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) TA3: TO-220, TF1:TO-220F1, TF3: TO-220F (3) L: Lead Free, G: Halogen Free

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■ MARKING INFORMATION

PACKAGE	MARKING
TO-220 TO-220F TO-220F1	

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{GS}=0	V_{DS}	800	V
Gate-Source Voltage		V_{GS}	±30	V
Drain-Gate Voltage	R_{GS}=20kΩ	V_{DGR}	800	V
Drain Current (Continuous)	Continuous	I_D	5.5	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	320	mJ
Power Dissipation	TO-220	P_D	125	W
	TO-220F /TO-220F1		40	
Derating Factor	TO-220		1	W/°C
	TO-220F /TO-220F1		0.32	
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55~150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Pulse width limited by safe operating area.
3. Starting T_J=25°C, I_D=I_{AR}, V_{DD}=50V

■ THERMAL DATA

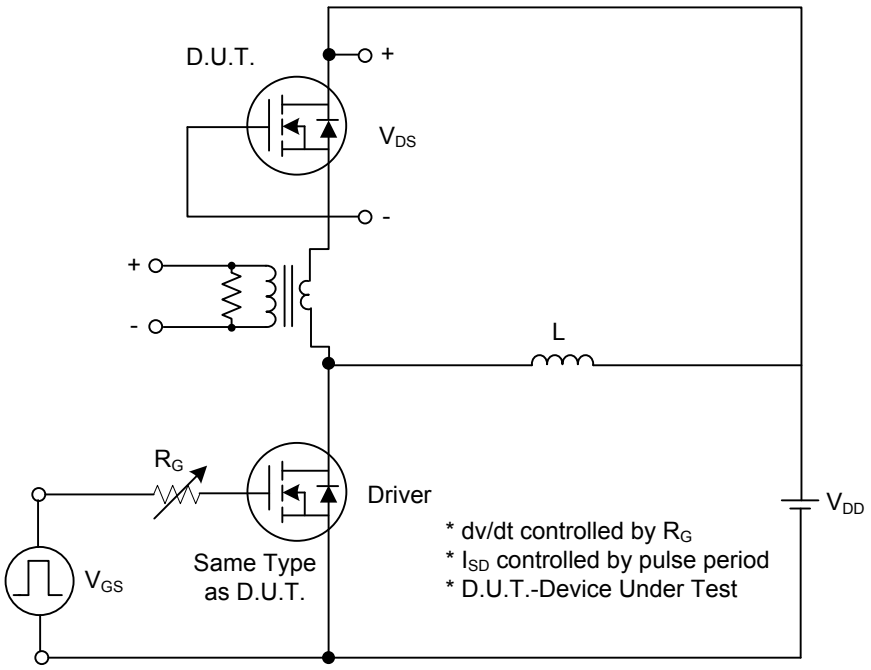
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	1	°C/W
	TO-220F /TO-220F1		3.12	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

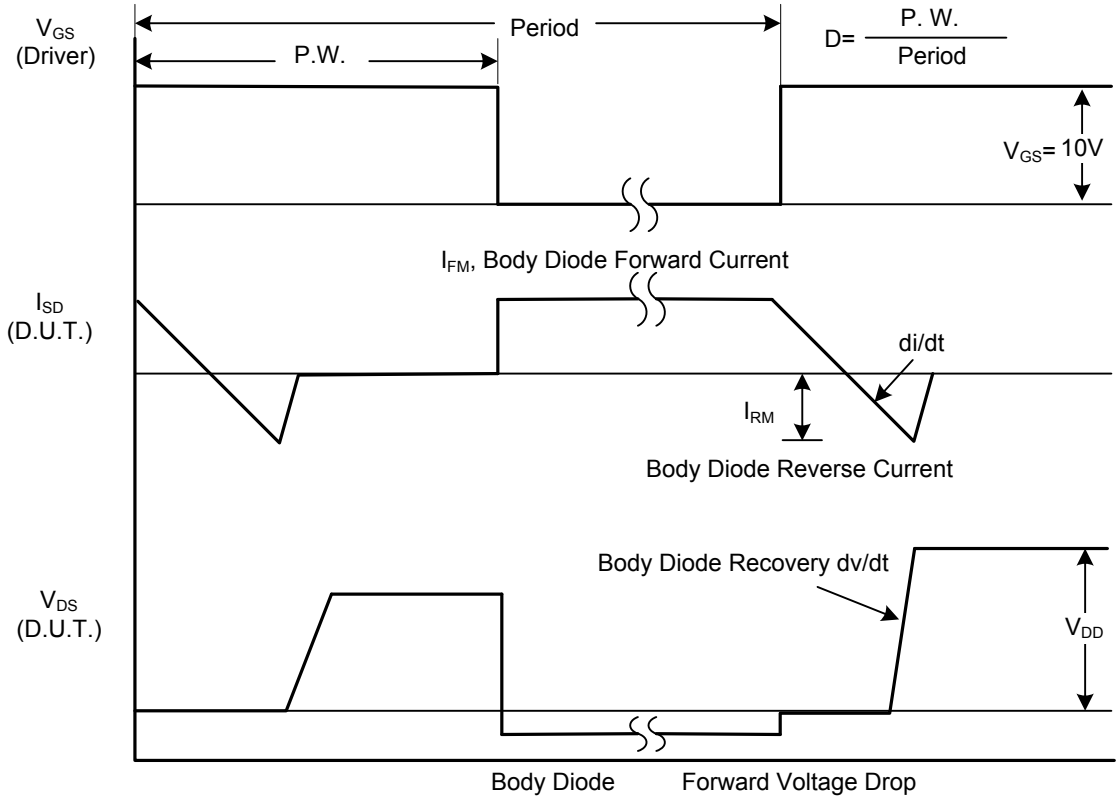
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	800			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=800V, V_{GS}=-0V			25	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V			+100	nA
	Reverse		V_{GS}=-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3		5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.5A		1.8	2.5	Ω
			V_{GS}=10V, I_D=2.5A, T_C=100°C			4	
On State Drain Current		$I_{D(ON)}$	V_{DS}>$I_{D(ON)}$×$R_{DS(ON)}$max,V_{GS}=10V	5			A
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		900	1450	pF
Output Capacitance		C_{OSS}			100	200	pF
Reverse Transfer Capacitance		C_{RSS}			14	20	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DD}=120V, I_D=5A (Note 1, 2)		145	170	nC
Gate to Source Charge		Q_{GS}			11		nC
Gate to Drain Charge		Q_{GD}			27		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DS}=30V, I_D=1A, R_G=50Ω V_{GS}=10V (Note 1, 2)		80	100	ns
Rise Time		t_R			135	150	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			240	260	ns
Fall-Time		t_F			120	140	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	I_{SD}=5.5A, V_{GS}=0V			2	V
Reverse Recovery Time		t_{rr}	I_{SD}=5.5A,dI/dt=100A/μs, V_{DD}=80V,T_J=150°C (Note 1)		700		ns
Reverse Recovery Charge		Q_{RR}			7.7		nC
Reverse Recovery Current		I_{RRM}			22		A
Source-Drain Current		I_{SD}				5.5	A
Source-Drain Current (Pulsed) (Note 1)		I_{SDM}				20	A

Notes: 1. Pulsed: Pulse duration=300μs, duty cycle 1.5%.
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

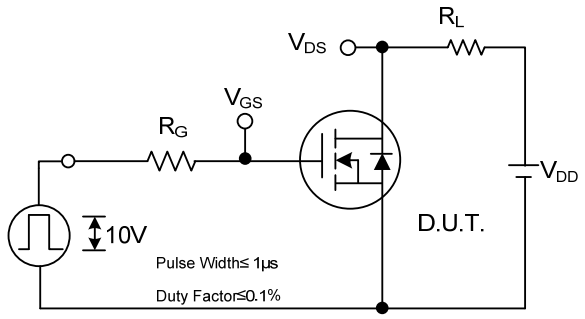


Peak Diode Recovery dv/dt Test Circuit

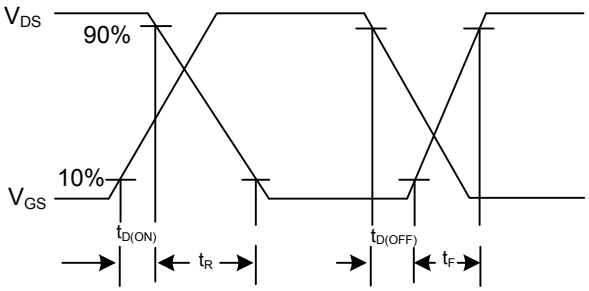


Peak Diode Recovery dv/dt Waveforms

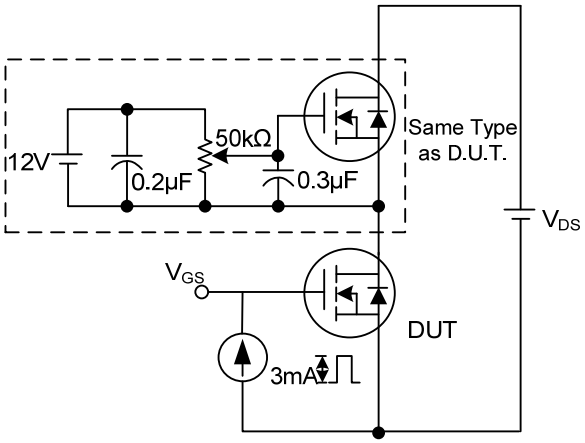
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



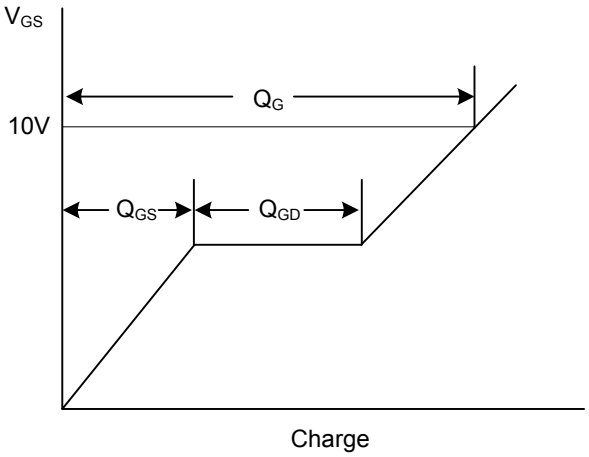
Switching Test Circuit



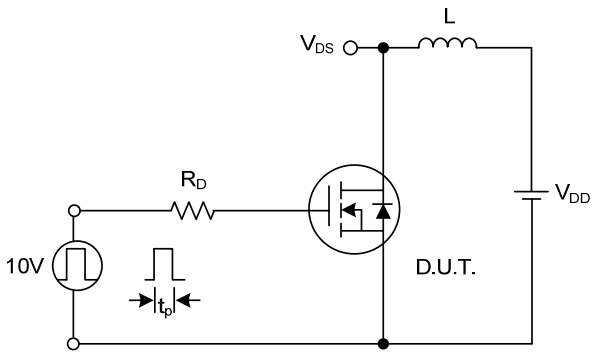
Switching Waveforms



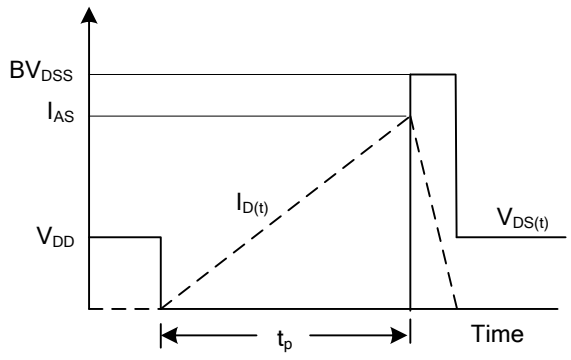
Gate Charge Test Circuit



Gate Charge Waveform



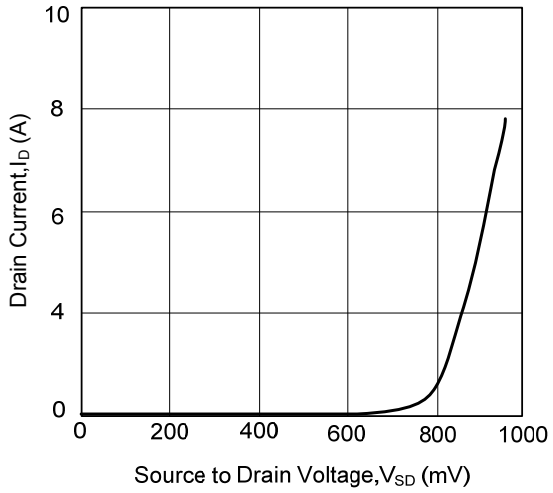
Unclamped Inductive Switching Test Circuit



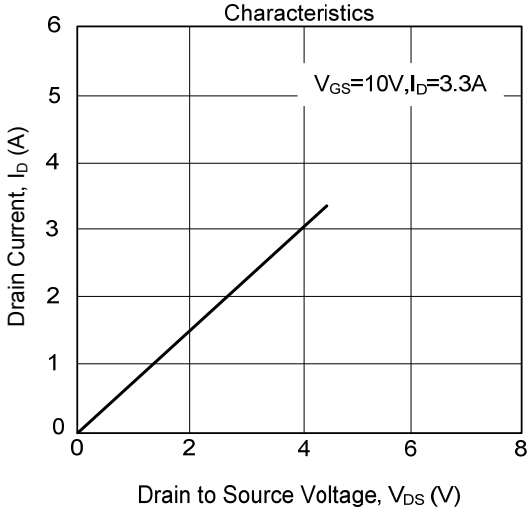
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

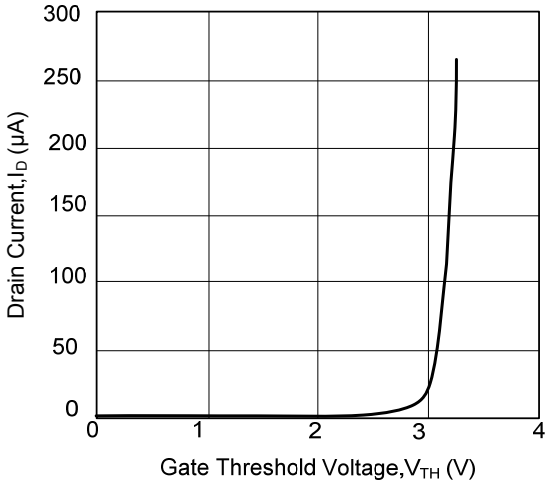
Drain Current vs. Source to Drain Voltage



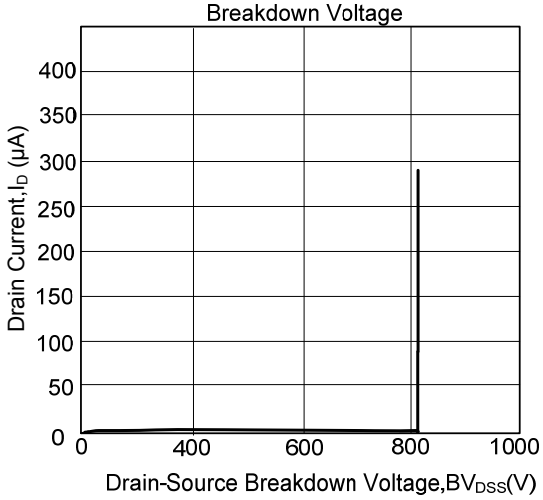
Drain-Source On State Resistance Characteristics



Drain Current vs. Gate Threshold Voltage



Drain Current vs. Drain-Source Breakdown Voltage



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